CGHV37400F

400 W, 3.5 - 3.7 GHz, 50-Ohm Input/Output Matched, GaN HEMT for S-Band Radar Systems

Package Type: 440217
PN: CGHV37400F

Description

The CGHV37400F is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically with high efficiency, high gain and wide bandwidth capabilities, which makes the CGHV37400F ideal for 3.5 - 3.7 GHz S-Band radar amplifier applications. The transistor is matched to 50-ohms on the input and 50-ohms on the output. The CGHV35400 is based on the high power density 50 V, 0.4 µm GaN-on-Silicon Carbide (SiC) foundry process. The transistor is supplied in a ceramic metal flange package, type 440217.

Typical Performance Over 3.5-3.7 GHz (T_C = 25°C) of Demonstration Amplifier

Parameter	3.5 GHz	3.6 GHz	3.7 GHz	Units
Output Power	555	560	555	W
Gain	11.4	11.5	11.4	dB
Drain Efficiency	55	555	55	%

Note: Measured in the CGHV37400F-AMP application circuit, under 100 µs pulse width, 10% duty cycle, P_{IN} = 46 dBm

Features

- 3.3 - 3.8 GHz Operation
- 525 W Typical Output Power
- 11.5 dB Power Gain
- 55% Typical Drain Efficiency
- 50 Ohm Internally Matched
- <0.3 dB Pulsed Amplitude Droop

Large Signal Models Available for ADS and MWO

RoHS compliant

Rev. 2.0, 2022-8-23

Absolute Maximum Ratings (not simultaneous)

Parameter	Symbol	Rating	Units	Conditions
Pulse Width	PW	100	µs	
Duty Cycle	DC	10	%	
Drain-Source Voltage	V_{DSS}	150	V	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2		
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Forward Gate Current	I_{GMAX}	80	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	24	A	
Soldering Temperature[2]	T_S	245	°C	
Screw Torque	τ	40	in-oz	
Pulsed Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.22	°C/W	100 µsec, 10%, 85°C , P_{DISS} = 418 W
Case Operating Temperature	T_C	-40, +125	°C	

Notes:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering

Electrical Characteristics

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1] (T_C = 25°C)						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 83.6 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–		V_{DS} = 50 V, I_D = 1.0 A
Saturated Drain Current[2]	I_{DS}	54.3	77.7	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	125	–	–	V_{DC}	V_{GS} = -8 V, I_D = 83.6 mA
RF Characteristics[3] (T_C = 25˚C, F_0 = 3.5 - 3.7 GHz unless otherwise noted)						
Output Power at 3.5 GHz	P_{OUT1}	400	525	–	W	V_{DD} = 50 V, I_{DQ} = 1000 mA, P_{IN} = 46 dBm
Output Power at 3.7 GHz	P_{OUT2}			–		
Drain Efficiency at 3.5 GHz	DE_1	50	55	–	%	
Drain Efficiency at 3.7 GHz	DE_2			–		
Small Signal Gain	S21	11.75	14	–	dB	V_{DD} = 50 V, I_{DQ} = 1000 mA, P_{IN} = -10 dBm
Input Return Loss	S11	–	-9	-4		
Output Return Loss	S22	–	-6			
Amplitude Droop	D	–	-0.3	–		V_{DD} = 50 V, I_{DQ} = 1000 mA, P_{IN} = 46 dBm
Output Stress Match[4]	VSWR	–	5:1	–	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 1000 mA, P_{IN} = 46 dBm Pulsed

Notes:
[1] Measured on wafer prior to packaging
[2] Scaled from PCM data
[3] Measured in CGHV37400F-AMP. Pulse Width = 100 µs, Duty Cycle = 10%
[4] The device is not recommended for 5:1 VSWR applications below 3.3 GHz

Typical Performance

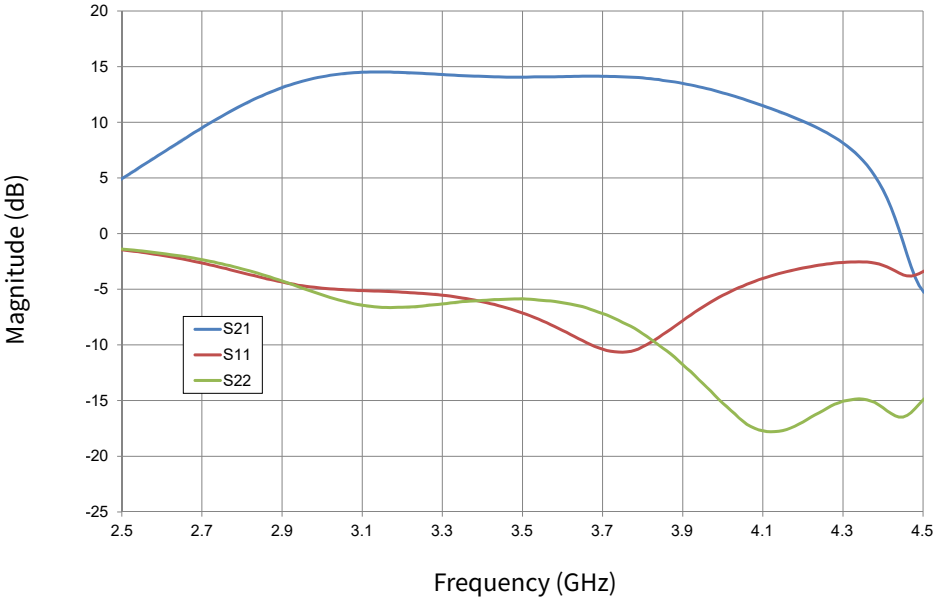


Figure 1. Typical Small Signal Gain and Return Losses vs Frequency
V_{DD} = 50 V, I_{DQ} = 1.0 A

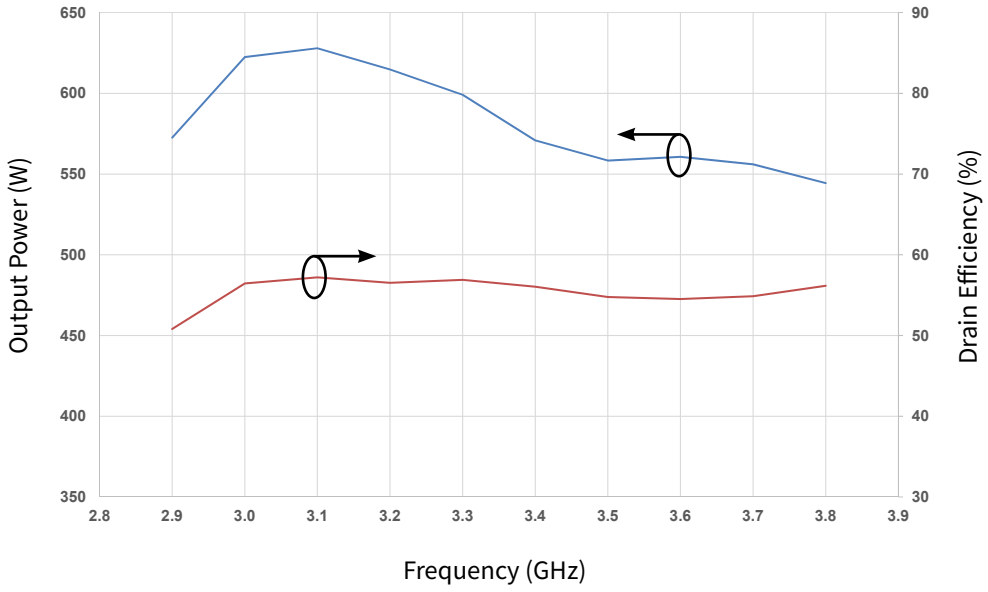


Figure 2. CGHV37400F Output Power and Drain Efficiency vs Frequency
V_{DD} = 50 V, I_{DQ} = 1.0 A, P_{IN} = 46 dBm, Pulse Width = 100µs, Duty Cycle = 10%,
T_{CASE} = 25°C

Typical Performance

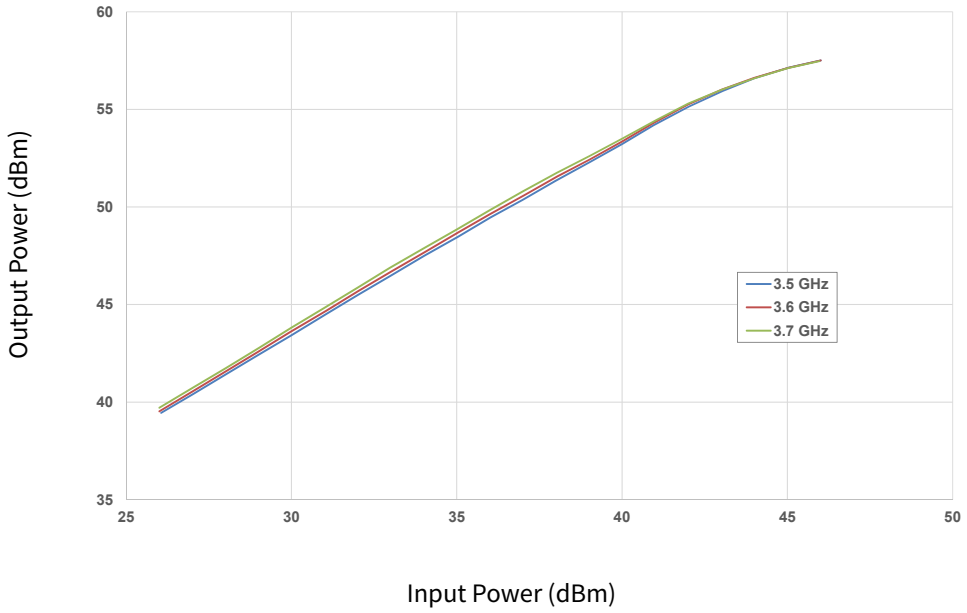


Figure 3. Typical Output Power vs Input Power of the CGHV37400F
V_{DD} = 50 V, I_{DQ} = 1.0 A, Pulse Width = 100µs, Duty Cycle = 10%, T_{CASE} = 25°C

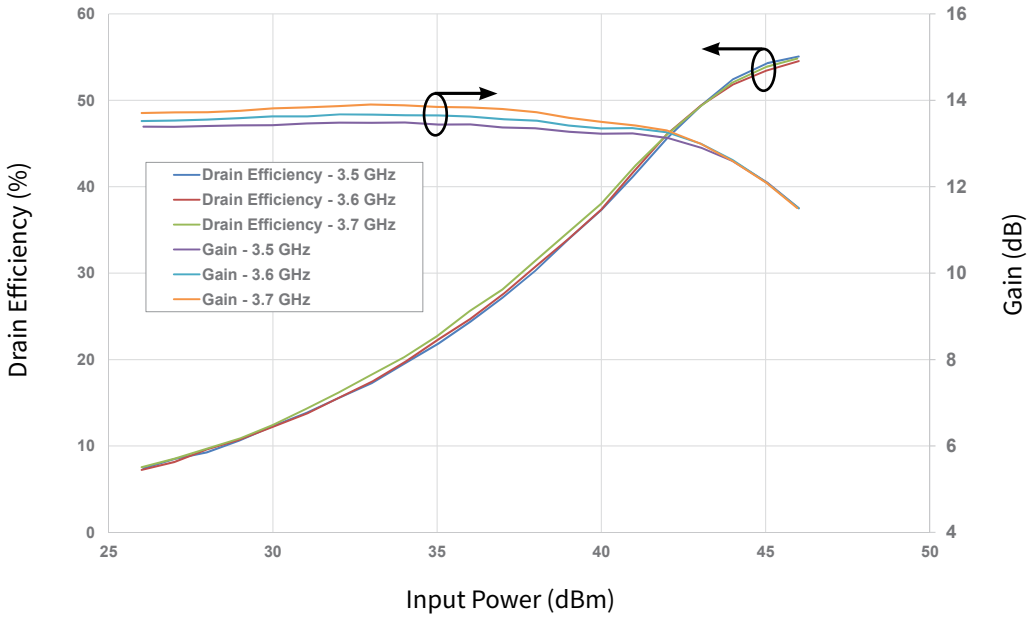


Figure 4. CGHV37400F Drain Efficiency and Gain vs Input Power
V_{DD} = 50 V, I_{DQ} = 1.0 A, Pulse Width = 100µs, Duty Cycle = 10%, T_{CASE} = 25°C

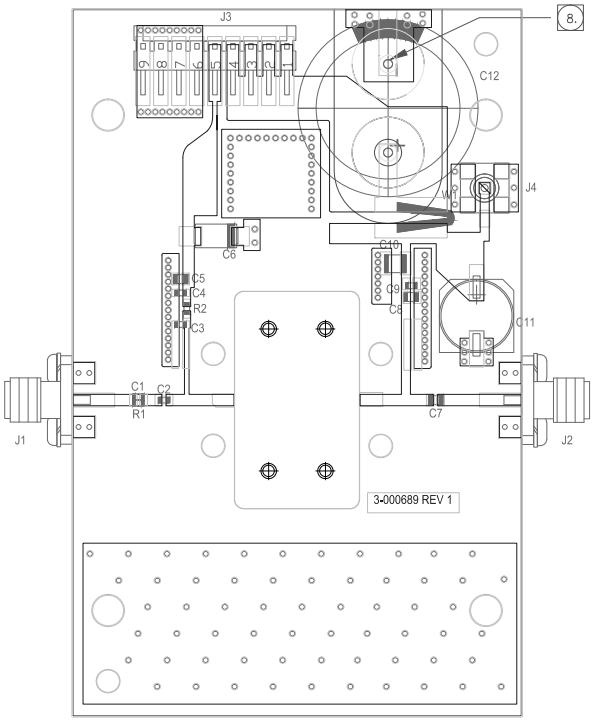
CGHV37400F-AMP Application Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 511, OHM, +/- 1%, 1/16W, 0603	1
R2	RES, 5.1, OHM, +/- 1%, 1/16W, 0603	1
C1	CAP, 6.8pF, +/-0.25%, 250V, 0603	1
C2, C7, C8	CAP, 10.0pF, +/-1%, 250V, 0805	3
C3	CAP, 10.0pF, +/-5%, 250V, 0603	1
C4, C9	CAP, 470pF, 5%, 100V, 0603, X	2
C5	CAP, 33000pF, 0805, 100V, X7R	1
C6	CAP, 10µF 16V TANTALUM	1
C10	CAP, 1.0µF, 100V, 10%, X7R, 1210	1
C11	CAP, 33µF, 20%, G CASE	1
C12	CAP, 3300µF, +/-20%, 100V, ELECTROLYTIC	1
J1,J2	CONN, SMA, PANEL MOUNT JACK, FL	2
J3	HEADER, RT>PLZ, 0.1CEN LK 9POS	1
J4	CONNECTOR; SMB, Straight, JACK, SMD	1
W1	CABLE, 18 AWG, 4.2	1
-	PCB, RO4350, 2.5 X 4.0 X 0.030	1
Q1	CGHV37400F	1

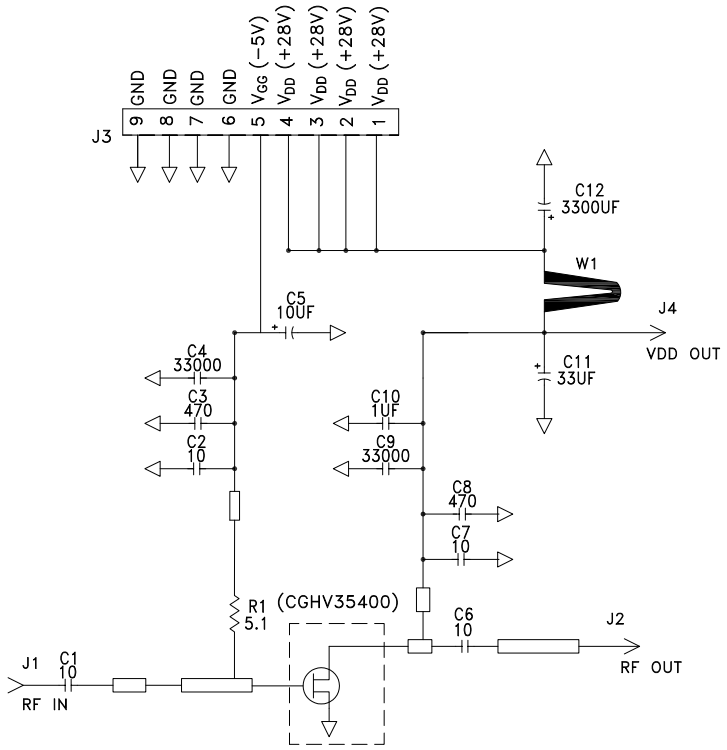
Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

CGHV37400F-AMP Application Circuit Outline

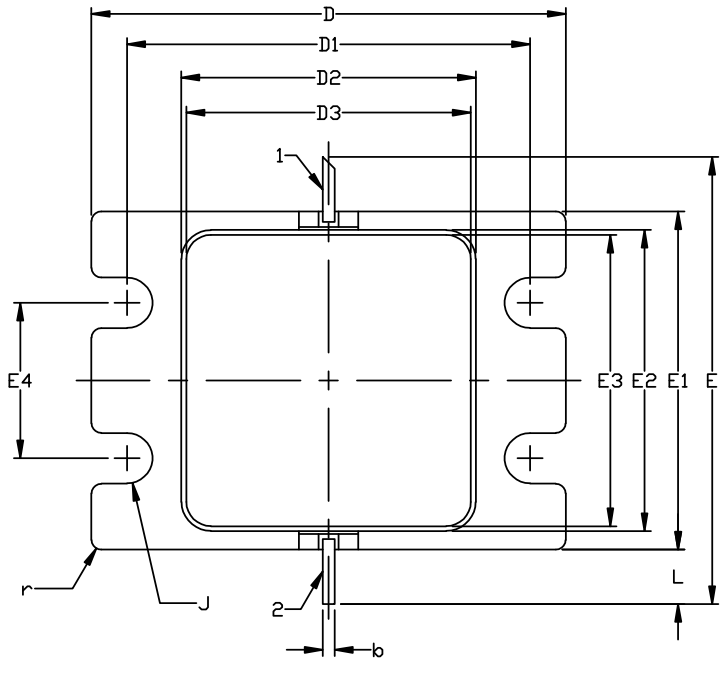


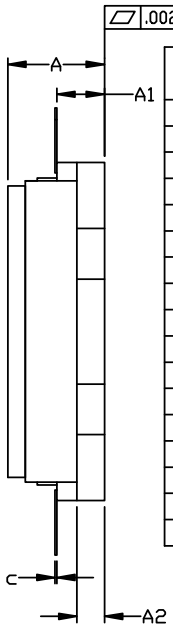
CGHV37400F-AMP Application Circuit Schematic



Product Dimensions CGHV37400F (Package Type — 440217)

NOTES: (UNLESS OTHERWISE SPECIFIED)
1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M-2009
2. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF .020 BEYOND EDGE OF LID
3. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF .008 IN ANY DIRECTION
4. ALL PLATED SURFACES ARE GOLD OVER NICKEL





1. GATE
2. DRAIN

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.188	0.198	4.78	5.03	
A1	0.088	0.100	2.24	2.54	2x
A2	0.049	0.061	1.24	1.55	
b	0.022	0.026	0.56	0.66	2x
c	0.002	0.006	0.05	0.15	
D	0.935	0.955	23.75	24.26	
D1	0.797	0.809	20.24	20.55	2x
D2	0.581	0.593	14.76	15.06	
D3	0.563	0.571	14.30	14.50	
E	0.906		23.01		REF
E1	0.679	0.691	17.25	17.55	
E2	0.604	0.616	15.34	15.65	
E3	0.586	0.594	14.88	15.09	
E4	0.309	0.321	7.85	8.15	2x
J	ø0.097	ø0.107	ø2.46	ø2.72	4x
L	0.090	0.130	2.29	3.30	2x
r	0.02 TYP		0.51 TYP		12x

Part Number System

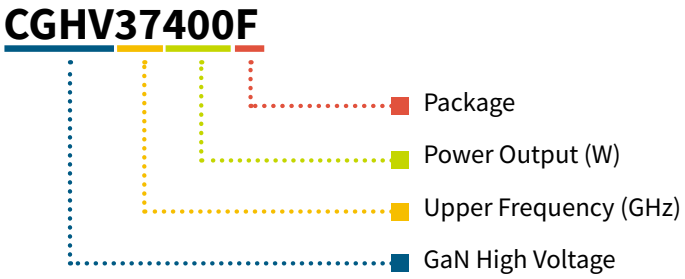


Table 1.

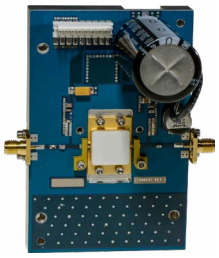
Parameter	Value	Units
Upper Frequency[1]	3.7	GHz
Power Output	400	W
Package	Flange	–

Note:
[1] Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value

Table 2.

Parameter	Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples	1A = 10.0 GHz 2H = 27.0 GHz

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV37400F	GaN HEMT	Each	
CGHV37400F-AMP	Test board with GaN HEMT installed	Each	

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